ABSTRACT

Silicon carbide matrix composite material (1) comprises silicon carbide matrix (2) as a host. The silicon carbide matrix (2) comprises first silicon carbide phase (3) of 0.1 to 10 μm average crystal grain diameter and second silicon carbide phase (4) of 0.01 to 2 μm average crystal grain diameter. In interstices of silicon carbide crystal grains constituting the silicon carbide matrix (2), liberated silicon phase (5) amounting to, for example, 5 to 50 mass% based on the composite material (1) is present continuously in network form. This fine structure enables realizing high strength and high toughness of the silicon carbide composite material (1).